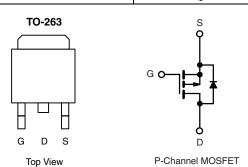


# Automotive P-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	- 60				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.0089				
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS}$ = - 4.5 V	0.0132				
I <sub>D</sub> (A)	- 110				
Configuration	Single				



#### **FEATURES**

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- 100 % R<sub>a</sub> and UIS Tested
- AEC-Q101 Qualified<sup>d</sup>
- Material categorization:
   For definitions of compliance please see www.vishav.com/doc?99912



FREE

ORDERING INFORMATION	
Package	TO-263
Lead (Pb)-free and Halogen-free	SQM110P06-8m9L-GE3

<b>ABSOLUTE MAXIMUM RATING</b>	<b>S</b> ( $T_C = 25  ^{\circ}C$ , unles	s otherwise noted	d)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		$V_{DS}$	- 60	V
Gate-Source Voltage		V <sub>GS</sub>	± 20	V
Continuous Drain Current	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	- 110	
Continuous Drain Current	T <sub>C</sub> = 125 °C		- 65	
Continuous Source Current (Diode Conducti	I <sub>S</sub>	- 120	А	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>		- 230
Single Pulse Avalanche Current		I <sub>AS</sub>	- 65	
Single Pulse Avalanche Energy	L = 0.1 mH	E <sub>AS</sub>	211	mJ
Maximum Dawar Dissinationh	T <sub>C</sub> = 25 °C	D_	230	W
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 125 °C		76	
Operating Junction and Storage Temperatur	e Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>c</sup>	$R_{thJA}$	40	°C/W	
nction-to-Case (Drain)		$R_{thJC}$	0.65	C/ VV	

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT		
Static							,	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		- 60	-	-	V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$		- 2.0	- 2.5	]	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = - 60 V	-	-	- 1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = - 60 V, T <sub>J</sub> = 125 °C	-	-	- 50	μΑ	
		$V_{GS} = 0 V$	V <sub>DS</sub> = - 60 V, T <sub>J</sub> = 175 °C	-	-	- 250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = - 10 V	V <sub>DS</sub> ≤ - 5 V	- 100	-	-	Α	
		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 30 A	-	0.0071	0.0089		
Drain-Source On-State Resistance <sup>a</sup>		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 30 A, T <sub>J</sub> = 125 °C	-	-	0.0147	Ω	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 30 A, T <sub>J</sub> = 175 °C	-	-	0.0189		
		V <sub>GS</sub> = - 4.5 V	I <sub>D</sub> = - 20 A	-	0.0105	0.0132		
Forward Transconductanceb	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 30 A		-	71	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>				5953	7450		
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = - 25 V, f = 1 MHz	-	750	940	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	583	730		
Total Gate Charge <sup>c</sup>	Qg			-	130	200		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} = -30 \text{ V}, I_{D} = -110 \text{ A}$	-	25	-	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	33	-		
Gate Resistance	R <sub>g</sub>	f = 1 MHz		1.2	2.6	4	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	15	25		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = - 30 V, $R_L$ = 0.27 $\Omega$ $I_D$ $\cong$ - 110 A, $V_{GEN}$ = - 10 V, $R_g$ = 1 $\Omega$		-	15	25	- ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	71	110		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	48	75		
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	- 230	Α	
Forward Voltage	$V_{SD}$	I <sub>F</sub> = - 85 A, V <sub>GS</sub> = 0 V		_	- 0.95	- 1.5	V	

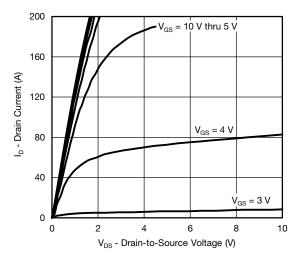
### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

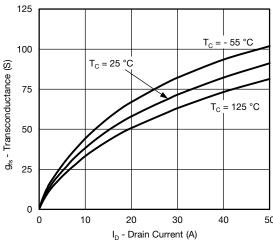
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



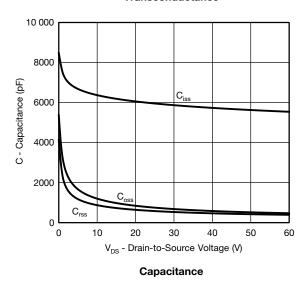
# **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

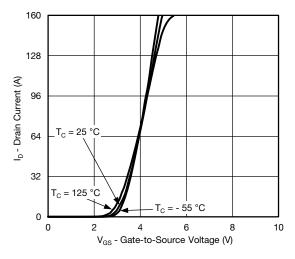


#### **Output Characteristics**

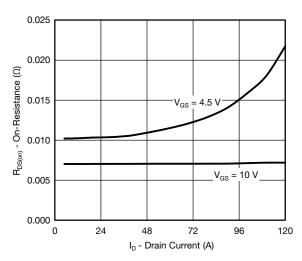


### Transconductance

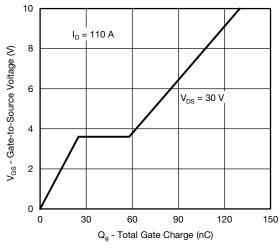




#### **Transfer Characteristics**

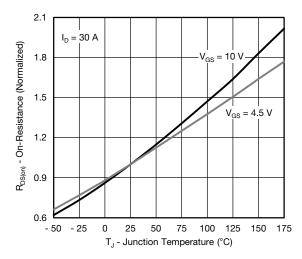


#### **On-Resistance vs. Drain Current**

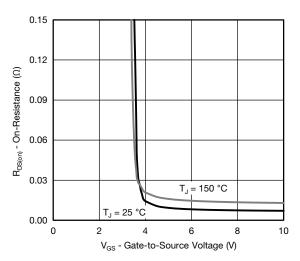




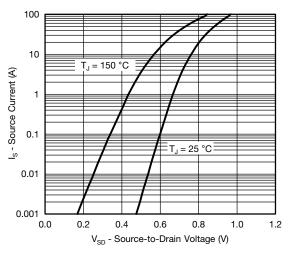
# **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



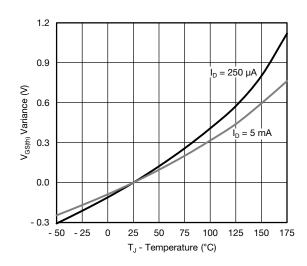
#### On-Resistance vs. Junction Temperature



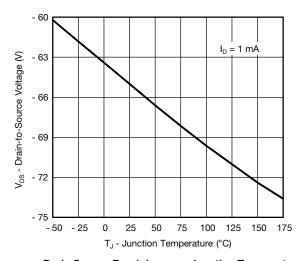
On-Resistance vs. Gate-to-Source Voltage



#### **Source Drain Diode Forward Voltage**



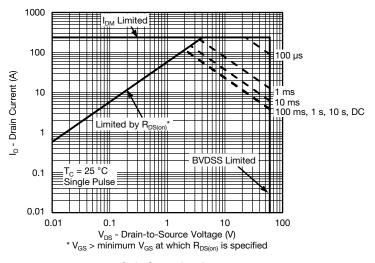
Threshold Voltage



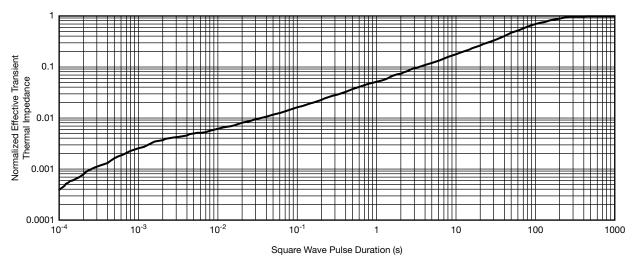
Drain Source Breakdown vs. Junction Temperature

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# **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



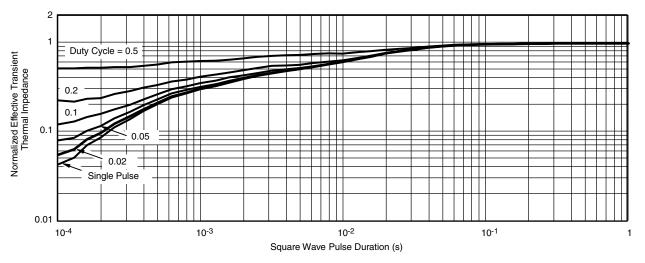
#### Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

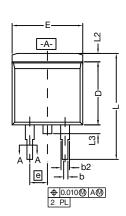
#### Note

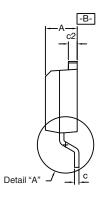
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction to Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

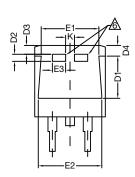
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# TO-263 (D<sup>2</sup>PAK): 3-LEAD

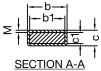








DETAIL A (ROTATED 90°)



_   <del>  -</del> b1 <del></del>	
≥ <del>                                    </del>	- -

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. \*: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6. This feature is for thick lead.

		INC	HES	MILLIMETERS		
DIM.		MIN.	MAX.	MIN.	MAX.	
Α		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1 0.220		0.240	5.588	6.096	
D2		0.038	0.042	0.965	1.067	
D3		0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	Е	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223 -		
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100	) BSC	2.54 BSC		
	K	0.045	0.055	1.143	1.397	
	L	0.575	0.625	14.605	15.875	
	L1	0.090	0.110	2.286	2.794	
	L2	0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
	L4	0.010 BSC		0.254 BSC		
	М	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13						

DWG: 5843





# RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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